Product Overview

FQD10N20C: Power MOSFET, N-Channel, QFET®, 200 V, 10 A, 360 mΩ , DPAK

For complete documentation, see the data sheet.

This N-Channel enhancement mode power MOSFET is produced using a proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

- 7.8A, 200V, RDS(on) = 360mΩ (Max.) @VGS = 10 V, ID = 3.9A
- Low gate charge (Typ. 20nC)
- Low Crss (Typ. 40.5pF)
- 100% avalanche tested

Applications

- LED TV
- CRT/RPTV
- Other Industrial

Part Electrical Specifications

Product	Pricing ($/Unit)	Compliance	Status	Channel Polarity	Configuration	$V_{(BR)DSS}$ Min (V)	V_{GS} Max (V)	$V_{GS(th)}$ Max (V)	I_D Max (A)	P_D Max (W)	$R_{DS(on)}$ Max @ V_{GS} = 2.5 V (mΩ)	$R_{DS(on)}$ Max @ V_{GS} = 4.5 V (mΩ)	$R_{DS(on)}$ Max @ V_{GS} = 10 V (mΩ)	Q_g Typ @ V_{GS} = 4.5 V (nC)	Q_g Typ @ V_{GS} = 10 V (nC)	C_{iss} Typ (pF)	Package Type
FQD10N20CTM	0.2669	Pb-free non AEC-Q and PPAP	Active	N-Channel	Single	200	±30	4	7.8	50	-	-	360	-	20	395	DPAK-3 / TO-252-3

For more information please contact your local sales support at www.onsemi.com.

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